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EDITORIAL

T-ED Retiring Editors	<i>J. D. Cressler</i>	4
Welcome to a New T-ED Editor	<i>J. D. Cressler</i>	5

REGULAR PAPERS

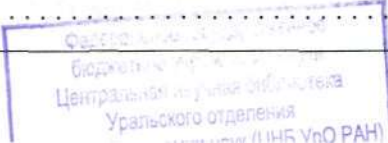
Silicon and Column IV Semiconductor Devices

Counterdoped Pocket Thickness Optimization of Gate-on-Source-Only Tunnel FETs	<i>K.-H. Kao, A. S. Verhulst, W. G. Vandenberghe, and K. De Meyer</i>	6
Revisited RF Compact Model of Gate Resistance Suitable for High-K/Metal Gate Technology	<i>B. Dormieu, P. Scheer, C. Charbuillet, H. Jaouen, and F. Danneville</i>	13
Coupling Mechanisms and Effects Between On-Chip Antenna and Inductor or Coplanar Waveguide	<i>T. Deng, Z. Chen, and Y. P. Zhang</i>	20
Design Optimization of Multigate Bulk MOSFETs	<i>B. Ho, X. Sun, C. Shin, and T.-J. K. Liu</i>	28
An Investigation on the Optimization and Scaling of Complementary SiGe HBTs	<i>P. S. Chakraborty, K. A. Moen, and J. D. Cressler</i>	34
Control of Resistance by Oxide on the Surface of Cu Interconnects With CuSiN and Ti-based Barrier Metal	<i>Y. Hayashi, N. Matsunaga, M. Wada, S. Nakao, K. Watanabe, S. Kato, A. Sakata, A. Kajita, and H. Shibata</i>	42
Comparison of SRAM Cells for 10-nm SOI FinFETs Under Process and Environmental Variations	<i>Z. Jakšić and R. Canal</i>	49
Al ₂ O ₃ Interface Engineering of Germanium Epitaxial Layer Grown Directly on Silicon	<i>Y. H. Tan, K. S. Yew, K. H. Lee, Y.-J. Chang, K.-N. Chen, D. S. Ang, E. A. Fitzgerald, and C. S. Tan</i>	56
Subthreshold Analog/RF Performance Enhancement of Underlap DG FETs With High- <i>k</i> Spacer for Low Power Applications	<i>K. Koley, A. Dutta, B. Syamal, S. K. Saha, and C. K. Sarkar</i>	63
Complementary Switching in Oxide-Based Bipolar Resistive-Switching Random Memory	<i>F. Nardi, S. Balatti, S. Larentis, D. C. Gilmer, and D. Ielmini</i>	70
Fabrication and Electrical Characterization of Fully CMOS-Compatible Si Single-Electron Devices	<i>P. J. Koppinen, M. D. Stewart, Jr., and N. M. Zimmerman</i>	78
Stochastic Variability in Silicon Double-Gate Lateral Tunnel Field-Effect Transistors	<i>G. Leung and C. O. Chui</i>	84
Improved Subthreshold and Output Characteristics of Source-Pocket Si Tunnel FET by the Application of Laser Annealing	<i>H.-Y. Chang, B. Adams, P.-Y. Chien, J. Li, and J. C. S. Woo</i>	92

(Contents Continued on Page 1)



FEM Model of Wraparound CNTFET With Multi-CNT and Its Capacitance Modeling	<i>M. R. K. Akanda and Q. D. M. Khosru</i>	97
Transport Gap in Dual-Gated Graphene Bilayers Using Oxides as Dielectrics	<i>K. Lee, B. Fallahazad, H. Min, and E. Tutuc</i>	103
Narrow-Width Effect on High-Frequency Performance and RF Noise of Sub-40-nm Multifinger nMOSFETs and pMOSFETs	<i>K.-L. Yeh and J.-C. Guo</i>	109
Orientalional Dependence in Device Performances of InAs and Si Nanowire MOSFETs Under Ballistic Transport	<i>K. Shimoida, Y. Yamada, H. Tsuchiya, and M. Ogawa</i>	117
Physical Modeling of the Capacitance and Capacitive Coupling Noise of Through-Oxide Vias in FDSOI-Based Ultra-High-Density 3-D ICs	<i>C. Xu and K. Banerjee</i>	123
Operating Voltage Constraints in 45-nm SOI nMOSFETs and Cascode Cores	<i>R. Arora and J. D. Cressler</i>	132
Contact-Induced Negative Differential Resistance in Short-Channel Graphene FETs	<i>R. Grassi, T. Low, A. Gnudi, and G. Baccarani</i>	140
Threshold Voltage Design and Performance Assessment of Hetero-Channel SRAM Cells	<i>V. P.-H. Hu, M.-L. Fan, P. Su, and C.-T. Chuang</i>	147
Fabrication of $\text{Si}_{1-x}\text{Ge}_x/\text{Si}$ pMOSFETs Using Corrugated Substrates for Improved I_{ON} and Reduced Layout-Width Dependence	<i>B. Ho, N. Xu, B. Wood, V. Tran, S. Chopra, Y. Kim, B.-Y. Nguyen, O. Bonnin, C. Mazur�e, S. Kuppurao, C.-P. Chang, and T.-J. K. Liu</i>	153
Compound Semiconductor Devices		
The Impact of Bias Conditions on Self-Heating in AlGaIn/GaN HEMTs	<i>S. Choi, E. R. Heller, D. Dorsey, R. Vetury, and S. Graham</i>	159
InP DHBTs Having Lateral and Sidewall Collector Schottky Contacts	<i>D. Cohen-Elias, A. Gavrilov, S. Cohen, S. Kraus, and D. Ritter</i>	163
A Parametric Study of InGaIn/GaN Nanorod Core-Shell LEDs	<i>M. Auf der Maur, F. Sacconi, and A. Di Carlo</i>	171
Position-Dependent Bulk Traps and Carrier Compensation in 4H-SiC Bipolar Junction Transistors	<i>M. Usman, M. Nawaz, and A. Hall�en</i>	178
Analysis of Contributing Factors for Determining the Reliability Characteristics of GaN-Based White Light-Emitting Diodes With Dual Degradation Kinetics	<i>E. Jung, M. S. Kim, and H. Kim</i>	186
Impact of Buffer Layer on Atomic Layer Deposited TiAlO Alloy Dielectric Quality for Epitaxial-GaAs/Ge Device Application	<i>G. K. Dalapati, C. K. Chia, C. Mahata, S. Krishnamoorthy, C. C. Tan, H. R. Tan, C. K. Maiti, and D. Chi</i>	192
Analysis of the GaAs/GaAsBi Material System for Heterojunction Bipolar Transistors	<i>Z. D. Marks, I. W. Haygood, and B. Van Zeghbroeck</i>	200
Characterization and Modeling of Cryogenic Ultralow-Noise InP HEMTs	<i>J. Schlee, H. Rodilla, N. Wadefalk, P.-�. Nilsson, and J. Grahn</i>	206
Enhanced AlGaIn/GaN MOS-HEMT Performance by Using Hydrogen Peroxide Oxidation Technique	<i>H.-Y. Liu, B.-Y. Chou, W.-C. Hsu, C.-S. Lee, J.-K. Sheu, and C.-S. Ho</i>	213
Micromachined Passive Bandpass Filters Based on GaAs Monolithic-Microwave-Integrated-Circuit Technology	<i>Z. Zhang and X. Liao</i>	221
Photoelectrical and Low-Frequency Noise Characteristics of ZnO Nanorod Photodetectors Prepared on Flexible Substrate	<i>T. P. Chen, S. J. Young, S. J. Chang, C. H. Hsiao, and S. L. Wu</i>	229
$\text{In}_{0.5}\text{Ga}_{0.5}\text{As}$ -Based Metal-Oxide-Semiconductor Capacitor on GaAs Substrate Using Metal-Organic Chemical Vapor Deposition	<i>H. Q. Nguyen, H. D. Trinh, E. Y. Chang, C. T. Lee, S. Y. Wang, H. W. Yu, C. H. Hsu, and C. L. Nguyen</i>	235
Junction-Temperature Determination in InGaIn Light-Emitting Diodes Using Reverse Current Method	<i>B. Q. Wu, S. Q. Lin, T.-M. Shih, Y. L. Gao, Y. J. Lu, L. H. Zhu, G. L. Chen, and Z. Chen</i>	241
Memory Devices and Technology		
Specifications of Nanoscale Devices and Circuits for Neuromorphic Computational Systems	<i>B. Rajendran, Y. Liu, J. Seo, K. Gopalakrishnan, L. Chang, D. J. Friedman, and M. B. Ritter</i>	246
Impact of Moisture From Passivation on Endurance and Retention of NAND Flash Memory	<i>Z.-S. Wang, T.-Y. Yin, T.-H. Ying, Y.-J. Lee, C.-Y. Lu, H. Arakawa, and C. J. Lin</i>	254
Thin Film Transistors		
Suppression of Drain-Induced Barrier Lowering in Silicon-on-Insulator MOSFETs Through Source/Drain Engineering for Low-Operating-Power System-on-Chip Applications	<i>T. Yamada, Y. Nakajima, T. Hanajiri, and T. Sugano</i>	260
Very Large Current Modulation in Vertical Heterostructure Graphene/hBN Transistors	<i>G. Fiori, S. Bruzzone, and G. Iannaccone</i>	268



Direct Band-to-Band Tunneling in Reverse Biased MoS ₂ Nanoribbon p-n Junctions	<i>R. K. Ghosh and S. Mahapatra</i>	274
Charge Distribution and Contact Resistance Model for Coplanar Organic Field-Effect Transistors	<i>C. H. Kim, Y. Bonnassieux, and G. Horowitz</i>	280
A Self-Consistent Electrothermal Model for Analyzing NBTI Effect in p-Type Poly-Si Thin-Film Transistors	<i>C.-H. Ho, G. Panagopoulos, and K. Roy</i>	288
Degradation of Polycrystalline Silicon TFT CMOS Inverters under AC Operation	<i>W. Chen, M. Wang, Y. Zhou, and M. Wong</i>	295
Optoelectronics, Displays, Imaging		
Application of MgCaO Cathode Layer to Plasma Display Panel for High Luminous Efficacy	<i>T.-H. Lee, H.-W. Cheong, O. Kwon, and K.-W. Whang</i>	301
Analysis of Gated CMOS Image Sensor for Spatial Filtering	<i>A. Spivak, A. Belenky, A. Fish, and O. Yadid-Pecht</i>	305
Fixed-Pattern-Noise Correction for an Integrating Wide-Dynamic-Range CMOS Image Sensor	<i>D. Das and S. Collins</i>	314
High-Performance Solution-Processed ZrInZnO Thin-Film Transistors	<i>P. T. Tue, T. Miyasako, J. Li, H. T. C. Tu, S. Inoue, E. Tokumitsu, and T. Shimoda</i>	320
Fabrication and Characterization of High-Mobility Solution-Based Chalcogenide Thin-Film Transistors	<i>I. Mejia, A. L. Salas-Villasenor, D. Cha, H. N. Alshareef, B. E. Gnade, and M. A. Quevedo-Lopez</i>	327
Color-Tunable and Phosphor-Free White-Light Multilayered Light-Emitting Diodes	<i>Y. F. Cheung and H. W. Choi</i>	333
Solid-State Power and High Voltage Devices		
High-Q Backside Silicon-Embedded Inductor for Power Applications in μ H and MHz Range	<i>R. Wu, J. K. O. Sin, and C. P. Yue</i>	339
A Novel Compact High-Voltage LDMOS Transistor Model for Circuit Simulation	<i>L. Shi, K. Jia, and W. Sun</i>	346
Design of Novel 300-V Field-MOS FETs With Low ON-Resistance for Analog Switch Circuits	<i>T. Miyoshi, T. Tominari, Y. Hayashi, M. Yoshinaga, T. Oshima, S. Wada, and J. Noguchi</i>	354
High-Performance p-Channel LDMOS Transistors and Wide-Range Voltage Platform Technology Using Novel p-Channel Structure	<i>S. Shimamoto, Y. Yanagida, S. Shirakawa, K. Miyakoshi, T. Oshima, J. Sakano, S. Wada, and J. Noguchi</i>	360
Numerical Evaluation of 10-kV Clustered Insulated Gate Bipolar Transistor in 4H-SiC	<i>K. G. Menon and E. M. S. Narayanan</i>	366
Materials, Processing, and Packaging		
Cu Interconnect Limitations and Opportunities for SWNT Interconnects at the End of the Roadmap	<i>A. Ceyhan and A. Naeemi</i>	374
Demonstration of a Subthreshold FPGA Using Monolithically Integrated Graphene Interconnects	<i>K.-J. Lee, H. Park, J. Kong, and A. P. Chandrakasan</i>	383
Solid-State Device Phenomena		
Self-Selection Unipolar HfO _x -Based RRAM	<i>X. A. Tran, W. Zhu, W. J. Liu, Y. C. Yeo, B. Y. Nguyen, and H. Y. Yu</i>	391
SiGe Channel Technology: Superior Reliability Toward Ultrathin EOT Devices—Part I: NBTI	<i>J. Franco, B. Kaczer, P. J. Roussel, J. Mitard, M. Cho, L. Witters, T. Grasser, and G. Groeseneken</i>	396
SiGe Channel Technology: Superior Reliability Toward Ultra-Thin EOT Devices—Part II: Time-Dependent Variability in Nanoscaled Devices and Other Reliability Issues	<i>J. Franco, B. Kaczer, M. Toledano-Luque, P. J. Roussel, T. Kauerauf, J. Mitard, L. Witters, T. Grasser, and G. Groeseneken</i>	405
New Insights Into Defect Loss, Slowdown, and Device Lifetime Enhancement	<i>M. Duan, J. F. Zhang, Z. Ji, W. D. Zhang, B. Kaczer, S. De Gendt, and G. Groeseneken</i>	413
Dependence of Read Margin on Pull-Up Schemes in High-Density One Selector–One Resistor Crossbar Array	<i>C.-L. Lo, T.-H. Hou, M.-C. Chen, and J.-J. Huang</i>	420
Comparison of Interfacial and Bulk Ionic Motion in Analog Memristors	<i>J. D. Greenlee, W. L. Calley, III, M. W. Moseley, and W. A. Doolittle</i>	427
Electrical Resistivity of Liquid Ge ₂ Sb ₂ Te ₅ Based on Thin-Film and Nanoscale Device Measurements	<i>K. Cil, F. Dirisaglik, L. Adnane, M. Wennberg, A. King, A. Faraclas, M. B. Akbulut, Y. Zhu, C. Lam, A. Gokirmak, and H. Silva</i>	433
Forming Kinetics in HfO ₂ -Based RRAM Cells	<i>P. Lorenzi, R. Rao, and F. Irrera</i>	438
On the Variability of the Front-/Back-Channel LF Noise in UTBOX SOI nMOSFETs	<i>S. D. dos Santos, T. Nicoletti, J. A. Martino, M. Aoulaiche, A. Veloso, M. Jurczak, E. Simoen, and C. Claeys</i>	444
Molecular and Organic Devices		
Performance Comparison of Conventional and Inverted Organic Bulk Heterojunction Solar Cells From Optical and Electrical Aspects	<i>D. Chen, C. Zhang, Z. Wang, J. Zhang, Q. Feng, S. Xu, X. Zhou, and Y. Hao</i>	451

Vacuum Electron Devices

Improved Efficiency of Backward-Wave Oscillator With an Inclined Electron Beam	<i>M. Sattorov, E. Khutoryan, K. Lukin, O. Kwon, and G.-S. Park</i>	458
The Design and Fabrication of Carbon-Nanotube-Based Field Emission X-Ray Cathode With Ballast Resistor	<i>Y. Sun, D. A. Jaffray, and J. T. W. Yeow</i>	464
High-Power Millimeter-Wave BWO Driven by Sheet Electron Beam	<i>Z. Wang, Y. Gong, Y. Wei, Z. Duan, Y. Zhang, L. Yue, H. Gong, H. Yin, Z. Lu, J. Xu, and J. Feng</i>	471
Field-Emission Characteristics of Selectively Grown CNTs	<i>C.-N. Tsai and H. Kirkici</i>	478
High-Power Tunable Terahertz Radiation by High-Order Harmonic Generation	<i>H. Gong, G. Travish, J. Xu, Y. Wei, J. Feng, and Y. Gong</i>	482
Nanodiamond Vacuum Field Emission Integrated Differential Amplifier	<i>S.-H. Hsu, W. P. Kang, J. L. Davidson, J. H. Huang, and D. V. Kerns, Jr.</i>	487
Enhancing Frequency-Tuning Ability of an Improved Relativistic Backward-Wave Oscillator	<i>W. Song, X. Zhang, C. Chen, J. Sun, and Z. Song</i>	494

BRIEFS

Bipolar Poisson Solution for Independent Double-Gate MOSFET	<i>A. Abraham, P. K. Thakur, and S. Mahapatra</i>	498
Physics-Based Solution for Electrical Resistance of Graphene Under Self-Heating Effect	<i>R. Verma, S. Bhattacharya, and S. Mahapatra</i>	502
High-Power Copper Gratings for a Sheet-Beam Traveling-Wave Amplifier at G-band	<i>C. D. Joye, J. P. Calame, A. M. Cook, and M. Garven</i>	506
Electron Transport in InAsSb-Based nBn Photodetector Structures	<i>G. A. Umana-Membreno, B. Klein, E. P. G. Smith, J. Antoszewski, E. Plis, S. M. Johnson, S. Krishna, D. R. Rhiger, and L. Faraone</i>	510
Characterization of Thermoelectric Properties of Heavily Doped n-Type Polycrystalline Silicon Carbide Thin Films	<i>M. I Lei and M. Mehregany</i>	513

CORRESPONDENCE

Errata to "Piecewise Linearization Technique for Compact Charge Modeling of Independent DG MOSFET"	<i>S. Jandhyala, A. Abraham, C. Anghel, and S. Mahapatra</i>	518
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ANNOUNCEMENTS

Call for Papers—Special Issue on GaN Electron Devices		519
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